

Description

The AOD403-HXY uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

G TO-252-2L (TO-252-2(DPAK))

General Features

 $V_{DS} = -30V I_{D} = -70 A$

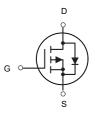
 $R_{DS(ON)} < 10 m\Omega$ @ V_{GS} =-10V

Application

Battery protection

Load switch

Uninterruptible power supply



P-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AOD403-HXY	TO-252-2L(TO-252-2(DPAK))	70P03 XXXYYYY	2500

Absolute Maximum Ratings (TC=25°C unless otherwise specified)

Symbol	Parameter	Rating		
VDS	Drain-Source Voltage	-30	V	
Vgs	Gate-Source Voltage	±20	V	
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ -10V ^{1,6}	-70	А	
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ -10V ^{1,6}	ntinuous Drain Current, V _{GS} @ -10V ^{1,6} -50		
Ірм	Pulsed Drain Current ²	Pulsed Drain Current ² -200		
EAS	Single Pulse Avalanche Energy ³	80	mJ	
las	Avalanche Current	-40	Α	
P _D @T _C =25°C	Total Power Dissipation ⁴	90	W	
Тѕтс	Storage Temperature Range	-55 to 175	°C	
TJ	Operating Junction Temperature Range	-55 to 175	°C	
	Thermal Resistance Junction-ambient ¹(t≦10S)	20	°C/W	
$R_{ heta}$ JA	Thermal Resistance Junction-ambient ¹ (Steady State)	50	°C/W	
R _θ Jc	Thermal Resistance Junction-case ¹	1.6	°C/W	



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-30			V	
		V _{GS} =-10V , I _D =-20A		7	10	mΩ	
RDS(ON)	Static Drain-Source On-Resistance ²	V _{GS} =-4.5V , I _D =-15A		11	18	mΩ	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-1.2		-2.5	V	
		V _{DS} =-24V , V _{GS} =0V , T _J =25℃			-1		
IDSS	Drain-Source Leakage Current	V _{DS} =-24V , V _{GS} =0V , T _J =55℃			-5	uA	
Igss	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V			±100	nA	
Rg	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz		1.2		Ω	
Qg	Total Gate Charge (-10V)			60			
Qgs	Gate-Source Charge	V _{DS} =-15V , V _{GS} =-10V		9		nC	
Qgd	Gate-Drain Charge	I _D =-18A		15			
Td(on)	Turn-On Delay Time			17			
Tr	Rise Time	V _{DD} =-15V V _{GS} =-10V		40		ns	
Td(off)	Turn-Off Delay Time	$R_G=3.3\Omega$,		55			
T _f	Fall Time	I _D =-20A		13			
Ciss	Input Capacitance			3450			
Coss	Output Capacitance	V _{DS} =-25V , V _{GS} =0V , f=1MHz		255		pF	
Crss	Reverse Transfer Capacitance			140			
ls	Continuous Source Current ^{1,5}	V _G =V _D =0V , Force Current			-70	Α	
VsD	Diode Forward Voltage ²	V _{GS} =0V , I _S =-1A , T _J =25℃			-1.2	V	
trr	Reverse Recovery Time	IF=-20A , di/dt=100A/µs ,		22		nS	
Q _{rr}	Reverse Recovery Charge	T _J =25℃		72		nC	

Note:

^{1.}The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.

^{2.}The data tested by pulsed , pulse width $\,\leq\,300\text{us}$, duty cycle $\,\leq\,2\%$

^{3.} The EAS data shows Max. rating . The test condition is V_{DD} =-50V, V_{GS} =-10V, L=0.1mH, I_{AS} =-40A

^{4.}The power dissipation is limited by 150 $^{\circ}\text{C}\,$ junction temperature

^{5.}The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation

^{6.} The maximum current rating is package limited.



Typical Characteristics

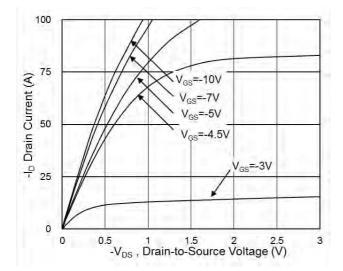


Fig.1 Typical Output Characteristics

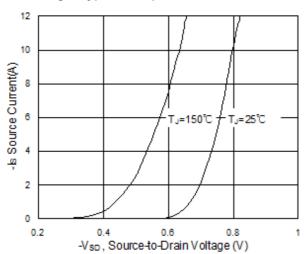


Fig.3 Forward Characteristics of Reverse

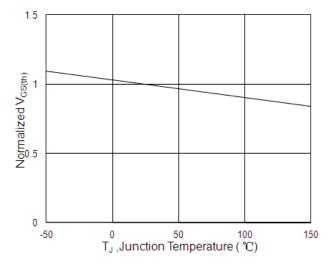


Fig.5 Normalized -V_{GS(th)} vs. T_J

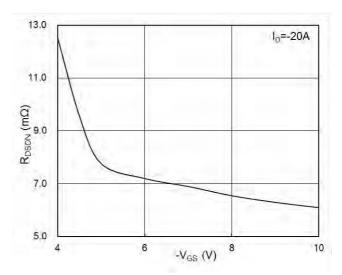


Fig.2 On-Resistance vs. Gate-Source Voltage

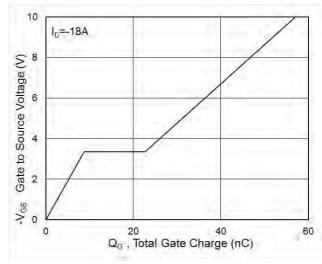


Fig.4 Gate-Charge Characteristics

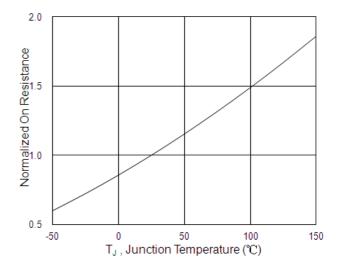
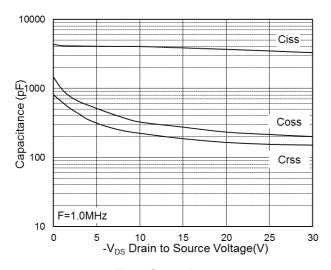


Fig.6 Normalized R_{DSON} vs. T_J



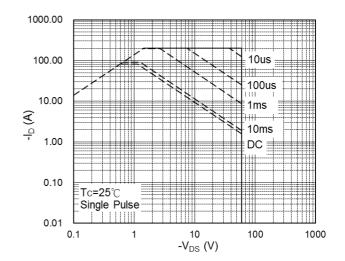


Fig.7 Capacitance

Fig.8 Safe Operating Area

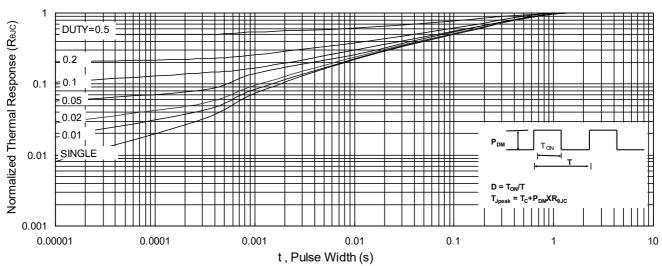


Fig.9 Normalized Maximum Transient Thermal Impedance

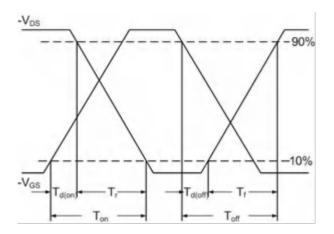


Fig.10 Switching Time Waveform

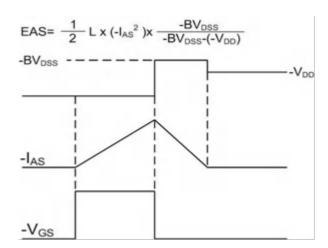
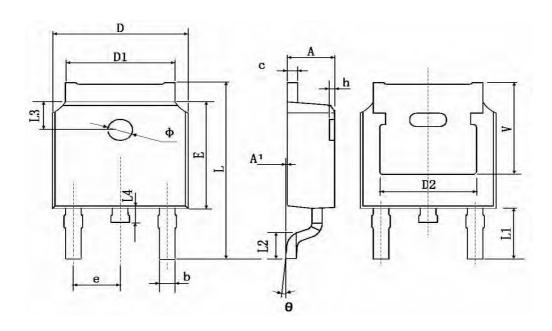


Fig.11 Unclamped Inductive Switching Waveform



TO-252-2L(TO-252-2(DPAK)) Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches			
	Min.	Max.	Min.	Max.		
Α	2.200	2.400	0.087	0.094		
A1	0.000	0.127	0.000	0.005		
b	0.660	0.860	0.026	0.034		
С	0.460	0.580	0.018	0.023		
D	6.500	6.700	0.256	0.264		
D1	5.100	5.460	0.201	0.215		
D2	4.830	4.830 TYP.		0.190 TYP.		
E	6.000	6.200	0.236	0.244		
е	2.186	2.386	0.086	0.094		
L	9.800	10.400	0.386	0.409		
L1	2.900	2.900 TYP.		0.114 TYP.		
L2	1.400	1.700	0.055	0.067		
L3		0 TYP. 0.063 TYP.				
L4	0.600	1.000	0.024	0.039		
Ф	1.100	1.300	0.043	0.051		
θ	0°	8°	0°	8°		
h	0.000	0.300	0.000	0.012		
V	5.350 TYP.		0.211 TYP.			



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